V.P. & R.P.T.P SCIENCE COLLEGE
INTERANAL EXAM
S.Y.B.Sc (6th semester.) ELECTRONICS
Time : 11.00 a.m. to 12.30 p.m.
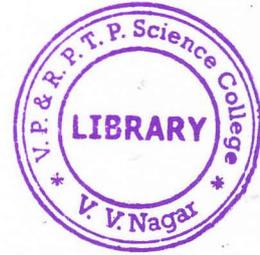
SUB. CODE:-US06CELE02   DATE:-07/03/2017

Q-1   Choose correct answer   **[3]**
1.   BJT memory is _____ Mos memory.
      (A) faster   (C) slower
      (B) veryslow   (D) none of above
2.   In static bipolar RAM 0 and 1 are sensed by presence and absence of _____.
      (A) current   (C) resistance
      (B)voltage   (D) none of above
3.   Flash type A/D converter is _____converter.
      (A) fastest   (C) slowest
      (B) random   (D) none of above

Q-2   Short answer type question.(attempt any two)   **[4]**

1.   Draw the circuit of weighted resistor type DAC.
2.   Draw the figure single transistor dynamic memory cell.
3.   Explain what do you understand by Program memory and Data memory.

Q-3   Draw a neat circuit of R-2R ladder type DAC and explain working of it.   **[6]**
                                OR
Q-3   Give an account of counter type A/D converter.   **[6]**

Q-4   Give an account of MASK programmed ROM.   **[6]**
                                OR
Q-4   Give an account of programmable Read only memory.   **[6]**

Q-5   Write a note RAM, ROM and PROM.   **[6]**
                                OR
Q-5   (A) Explain in detail ROM organization drawing block diagram. [3] **[6]**
               (B) Explain ROM diagram in detail.   [3]

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